

### M-100G-04-03 W4



SPECIFICATIONS Test conditions: CW operation at 25°C									
Parameters	Symb.	Min.	Тур.	Max.	Unit				
Total Output power	Pout		30	75	mW				
Central wavelength	λ <sub>c</sub>	1305	1310	1332	nm				
Optical Power per channel		0.8	1.7	2.7	mW				
Number of channels (<-3dB difference)		4	8	16					
Channel spacing		102.4	103.5	105.2	GHz				
Individual FP mode (channel) RIN (averaged in 0.1-8GHz range)			-135	-135	dB/Hz				
Laser Diode power conversion efficiency (P <sub>out</sub> / I <sub>op</sub> / V <sub>f</sub> )	WPE	5.3	6	8	%				
LD Threshold current	I <sub>th</sub>	28	35	50	mA				
LD Operating current	I <sub>op</sub>		180	300	mA				
Bandwidth	f <sub>-3dB</sub>		8	11.46	nm				
Bias Voltage	Va	0	1.6	5	V				
Operation Temperature		80	100		°C				

#### **Sample Description:**

200GHz Mode-locked Laser samples are 4th order colliding pulse mode-locked laser (CPML) based on InAs/GaAs

QD gain structure.

#### **Features**

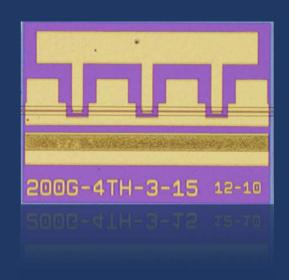
1300 – 1340nm wavelength

Mode spacing at 200 GHz

Single comb line power up to 17mW

Temperature operation range 10°C-50°C

QD active layer



SPECIFICATIONS Test conditions : CW at 25 °C	Symb.	Min.	Тур.	Max.	Unit.
Threshold Current	I <sub>th</sub>	28(0V)	30	57(-3V)	mA
Slope Efficiency	η	0.30	0.40	0.41	W/A
Max Output Power	P <sub>out</sub>	33.2(-3V)	56	61.5(0V)	mW
Reverse Bias Voltage	V <sub>R</sub>	0	0.9	3	V
Conversion Efficiency	WPE	-	-	14.8%	-
Center Wavelength	λ <sub>C</sub>	1300	1330	1335	nm
Channel Spacing	FSR	197.91	200	201.29	GHz
Optical Power per Channel*	Р	8.7	10	17.8	mW
Extinction Ratio	ER	-	40	45	dB
Number of channels	-	-	4	5	-
Bandwidth (3dB)	Δλ <sub>-3dB</sub>	-	-	3.54	nm